

NPN Small-Signal Darlington Transistor

BSP52T1G, BSP52T3G, SBSP52T1G

This NPN small signal Darlington transistor is designed for use in switching applications, such as print hammer, relay, solenoid and lamp drivers. The device is housed in the SOT-223 package, which is designed for medium power surface mount applications.

Features

- The SOT-223 Package can be soldered using wave or reflow. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Available in 12 mm Tape and Reel
Use BSP52T1 to Order the 7 Inch/1000 Unit Reel
- PNP Complement is BSP62T1
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CES}	80	V
Collector-Base Voltage	V_{CBO}	90	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	1.0	A
Total Power Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	0.8 6.4	W mW/ $^\circ\text{C}$
Total Power Dissipation (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.25 10	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance (Note 1) Junction-to-Ambient	$R_{\theta JA}$	156	$^\circ\text{C}/\text{W}$
Thermal Resistance (Note 2) Junction-to-Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Maximum Temperature for Soldering Purposes Time in Solder Bath	T_L	260 10	$^\circ\text{C}$ Sec

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

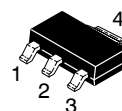
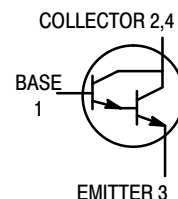
1. Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.
2. Device mounted on a FR-4 glass epoxy printed circuit board using 1 cm² pad.



ON Semiconductor®

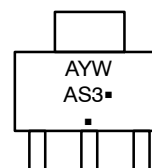
www.onsemi.com

MEDIUM POWER NPN SILICON SURFACE MOUNT DARLINGTON TRANSISTOR



SOT-223
CASE 318E
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
AS3 = Specific Device Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BSP52T1G, SBSP52T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
BSP52T3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSP52T1G, BSP52T3G, SBSP52T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
-----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector-Base Breakdown Voltage ($I_C = 100\ \mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	90	–	–	V
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	–	–	V
Collector-Emitter Cutoff Current ($V_{CE} = 80\ \text{V}$, $V_{BE} = 0$)	I_{CES}	–	–	10	μA
Emitter-Base Cutoff Current ($V_{EB} = 4.0\ \text{V}$, $I_C = 0$)	I_{EBO}	–	–	10	μA

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = 150\ \text{mA}$, $V_{CE} = 10\ \text{V}$) ($I_C = 500\ \text{mA}$, $V_{CE} = 10\ \text{V}$)	h_{FE}	1000 2000	– –	– –	–
Collector-Emitter Saturation Voltage ($I_C = 500\ \text{mA}$, $I_B = 0.5\ \text{mA}$)	$V_{CE(sat)}$	–	–	1.3	V
Base-Emitter Saturation Voltage ($I_C = 500\ \text{mA}$, $I_B = 0.5\ \text{mA}$)	$V_{BE(sat)}$	–	–	1.9	V

SWITCHING CHARACTERISTICS

Rise Time ($V_{CC} = 10\ \text{V}$, $I_C = 150\ \text{mA}$, $I_{B1} = 0.15\ \text{mA}$)	t_r	–	155	–	ns
Delay Time ($V_{CC} = 10\ \text{V}$, $I_C = 150\ \text{mA}$, $I_{B1} = 0.15\ \text{mA}$)	t_d	–	205	–	ns
Storage Time ($V_{CC} = 10\ \text{V}$, $I_C = 150\ \text{mA}$, $I_{B1} = 0.15\ \text{mA}$, $I_{B2} = 0.15\ \text{mA}$)	t_s	–	420	–	ns
Fall Time ($V_{CC} = 10\ \text{V}$, $I_C = 150\ \text{mA}$, $I_{B1} = 0.15\ \text{mA}$, $I_{B2} = 0.15\ \text{mA}$)	t_f	–	365	–	ns

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

BSP52T1G, BSP52T3G, SBSP52T1G

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

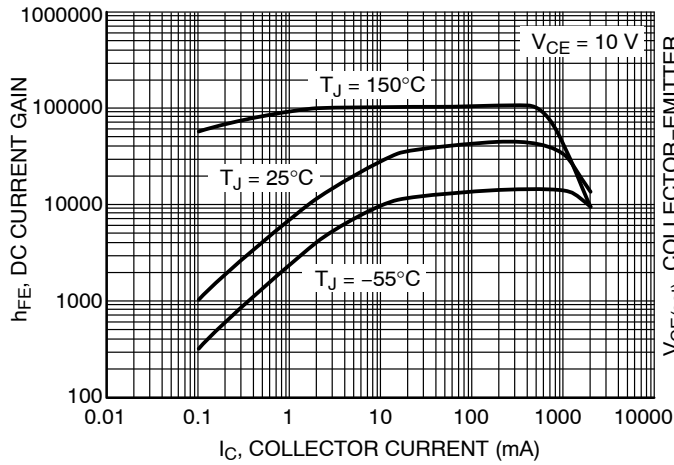


Figure 1. DC Current Gain

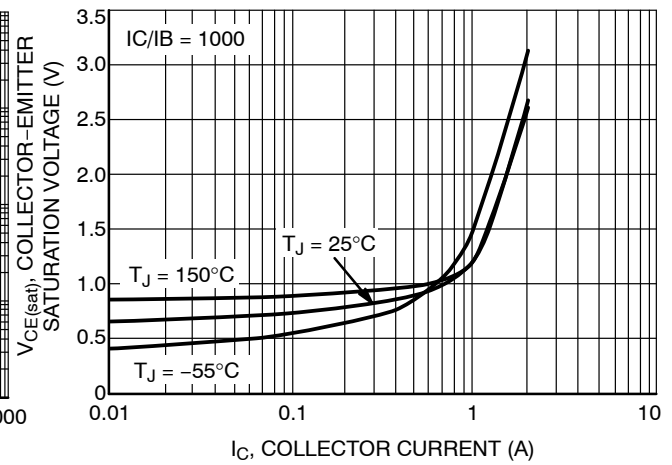


Figure 2. Collector-Emitter Saturation Voltage

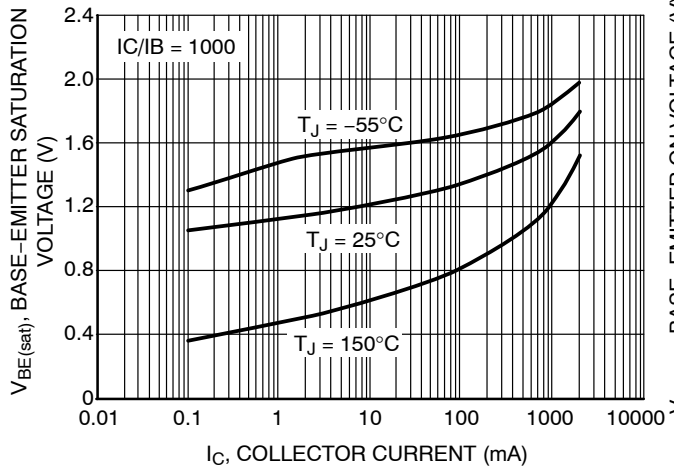


Figure 3. Base-Emitter Saturation Voltage

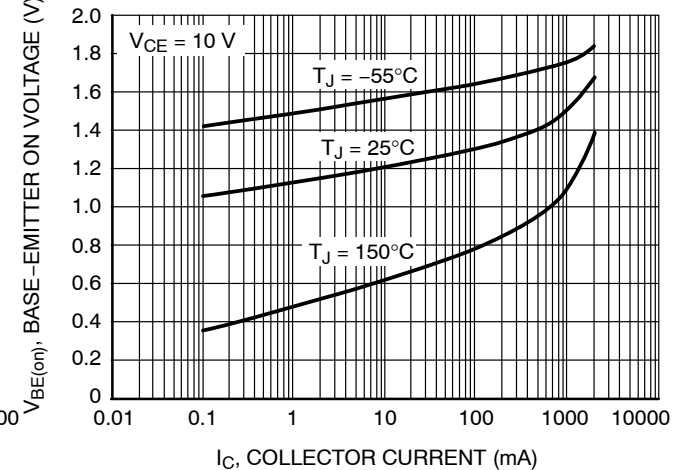


Figure 4. Base-Emitter ON Voltage

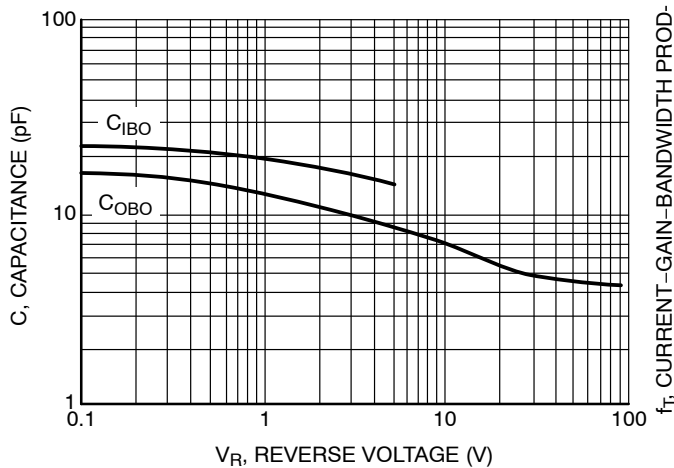


Figure 5. Capacitance

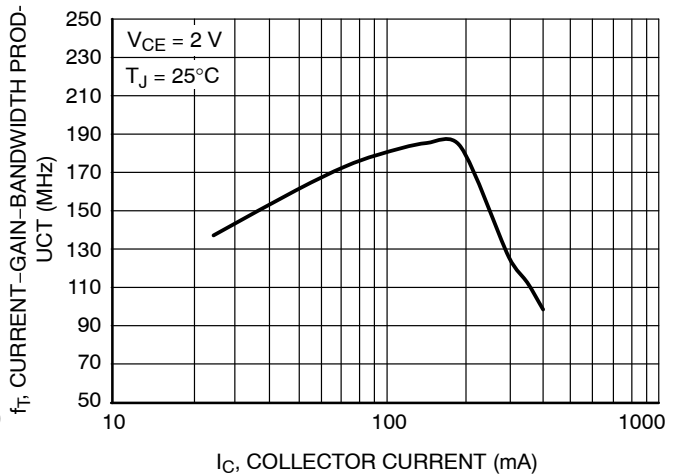


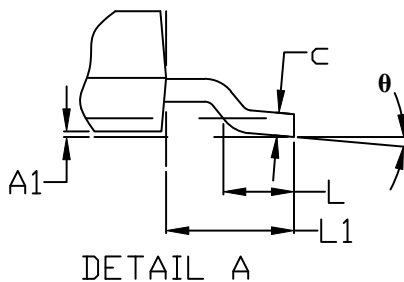
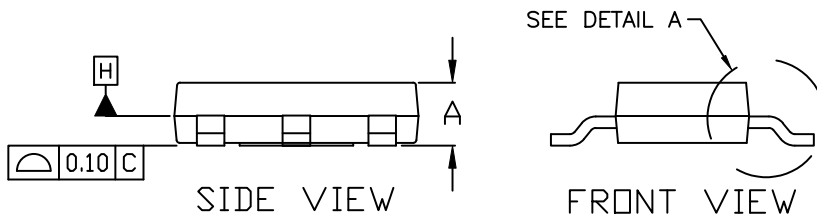
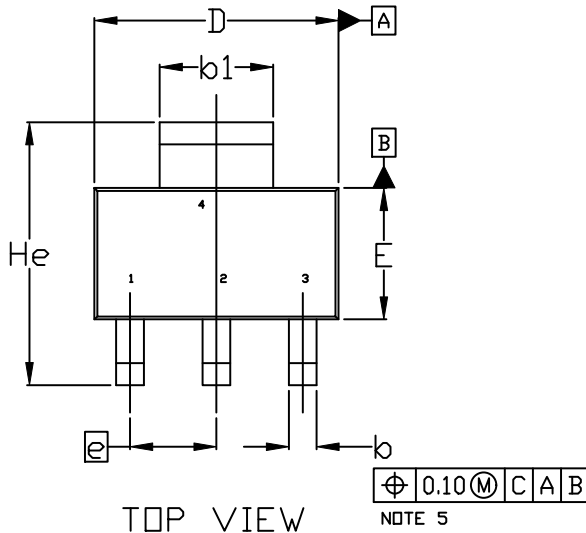
Figure 6. Current Gain Bandwidth Product vs. Collector Current



SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

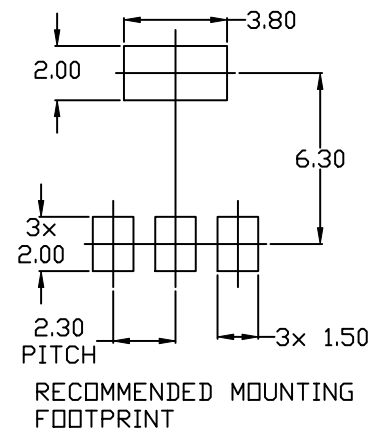
DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223 (TO-261)	PAGE 1 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

**GENERIC
MARKING DIAGRAM***



A = Assembly Location
 Y = Year
 W = Work Week
 XXXXX = Specific Device Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)
 *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223 (TO-261)	PAGE 2 OF 2

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative